EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3504	438/151	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 22:45
L2	4439	438/149	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/03/13 22:45
L3	5	resist near area with substrate with mask same implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:46
L4	43252	pixel electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:46
L5	10967	pixel electrode and mask and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:46
L6	7101	pixel electrode and mask and semiconductor and active matrix	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:47
L7	3570	pixel electrode and mask with resist and semiconductor and active matrix	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:47

L8	3	pixel electrode and mask area with resist and semiconductor and active matrix	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:48
L9	22	257/e21.582	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 22:53
L10	577	438/510	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:20
L11	249	438/515	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:20
L12	1	ushitani-hitomi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:20
L13	59	nagao-shou.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:21
L14	87	iwabuchi-tomoyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:21
L15	145	(12 or 13 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2008/03/13 23:22

S1	5	mask near area with well adj known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13
S2	0	mask near area with known same impant $6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 14:20
S3	0	mask near area with known and impant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 14:20
S4	0	mask with area with known and impant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 14:20
S5	153	mask with area with known and implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 14:21
S6	40	mask with area with known same implant $6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 15:14
S7	0	mask with area with design with known same implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 15:14
S8	20	mask with area with design with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:51

S9	84	mask near area with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:52
S10	4	mask near area with known same implant $6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:54
S11	0	mask near percent with area with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:55
S12	1	mask with percent with area with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:55
S13	151	mask with percent with area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:56
S14	8	mask with percent with area and implant $6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 16:59
S15	12	mask near percent with area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 11:13
S16	1	mask near percent with area and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 17:33

S17	1	mask near percent near area and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 17:34
S18	5	mask near percent near area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 17:41
S19	5	("1" or "2" or "3" or "4" or "5" or "6" or "7" or "8" or "9" or "10" or "11" or "12" or "13" or "14" or "15") adj percent with mask near area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13
S20	5	("1" or "2" or "3" or "4" or "5" or "6" or "7" or "8" or "9" or "10" or "11" or "12" or "13" or "14" or "15") near percent with mask near area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 17:46
S21	12	("1" or "2" or "3" or "4" or "5" or "6" or "7" or "8" or "9" or "10" or "11" or "12" or "13" or "14" or "15") near percent same mask near area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 17:58
S22	7	("1" or "2" or "3" or "4" or "5" or "6" or "7" or "8" or "9" or "10" or "11" or "12" or "13" or "14" or "15") near percent same mask area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:19
S23	90	dop$3 same mask area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:20

S24	0	dop$3 same percent with mask area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:20
S25	0	dop$3 same percent same mask area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:21
S26	90	dop$3 same mask adj area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13
S27	0	dop$3 same mask adj area with percent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:21
S28	0	dop$3 same mask adj area with "%"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:22
S29	30	dop$3 same mask adj area and kev	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:27
S30	1	implant with mask adj area and kev	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:29
S31	1234	mask$3 with percentage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:30

S32	14	mask$3 with percentage same implant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13
S33	0	mask$3 near percent $3 same implant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:34
S34	186	mask$3 near percent $3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:34
S35	55	mask$3 near percent $3 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:34
S36	0	mask$3 near percent $3 and semiconductor and kev	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:34
S37	5	mask$3 near percent $3 and semiconductor and implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/09 18:35
S38	105	resist with area with proportion	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 15:48
S39	7	resist with area with proportion same mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:02

S40	1409	resist with area with substrate same mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:02
S41	1094	resist with area with substrate with mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:03
S42	12	resist adj area with substrate with mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:02
S43	209	resist with area with substrate with mask same implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:04
S44	5	resist near area with substrate with mask same implant$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:04
S45	0	resist near area with substrate with mask with percent$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:05
S46	8	resist near area with percent$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:06
S47	76	resist with area and coverage with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:06

S48	10	resist with area same coverage with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/02/10 17:06
S49	3946	tft and mask and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 11:13
S50	1	tft and mask with area with known and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 11:14
S51	125	semiconductor and mask with area with known and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 11:17
S52	200	tft and mask with known and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 11:20
S53	11	tft and mask with area same known and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 12:10
S54	38	substrate with one square meter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 12:11
S55	0	tft substrate with one square meter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 12:11

S56	6	tft and substrate with one square meter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 13:38
S57	0	semiconductor substrate with one square meter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 13:38
S58	2	semiconductor same substrate with one square meter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/03/20 13:38
S59	1666	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 10:13
S60	1355	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 10:13
S61	1906	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 10:13
S62	1478	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 10:13
S63	5	mask near area with well adj known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13

S64	19	mask$3 with percentage same implant	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:13
S65	95	dop$3 same mask adj area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/09/18 10:14
S66	3297	mask area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/03/21 14:18
S67	322	mask area and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/03/21 14:19
S68	9	mask area with ratio and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/03/21 14:23
S69	94	mask with area with ratio and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/03/21 14:23
S70	15	mask with area with ratio with wafer and implant$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2007/03/21 14:23

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